### FAIRCHILD

SEMICONDUCTOR TM

# 74VCX164245 Low Voltage 16-Bit Dual Supply Translating Transceiver with 3-STATE Outputs

#### **General Description**

The VCX164245 is a dual supply, 16-bit translating transceiver that is designed for two way asynchronous communication between busses at different supply voltages by providing true signal translation. The supply rails consist of V<sub>CCB</sub>, which is the higher potential rail operating at 2.3V to 3.6V and V<sub>CCA</sub>, which is the lower potential rail operating at 1.65V to 2.7V. (V<sub>CCA</sub> must be less than or equal to V<sub>CCB</sub> for proper device operation.) This dual supply design allows for translation from 1.8V to 2.5V busses to busses at a higher potential, up to 3.3V.

The Transmit/Receive (T/ $\overline{R}$ ) input determines the direction of data flow. Transmit (active-HIGH) enables data from A Ports to B Ports. Receive (active-LOW) enables data from B Ports to A Ports. The Output Enable ( $\overline{OE}$ ) input, when HIGH, disables both A and B Ports by placing them in a High-Z condition. The A Port interfaces with the lower voltage bus (1.8V – 2.5V). The B Port interfaces with the higher voltage bus (2.7V – 3.3V). Also the VCX164245 is designed so that the control pins (T/ $\overline{R}_n, \overline{OE}_n$ ) are supplied by  $V_{CCB}.$ 

The 74VCX164245 is suitable for mixed voltage applications such as notebook computers using a 1.8V CPU and 3.3V peripheral components. It is fabricated with an Advanced CMOS technology to achieve high speed operation while maintaining low CMOS power dissipation.

#### Features

■ Bidirectional interface between busses ranging from 1.65V to 3.6V

March 2000

Revised June 2001

- Supports Live Insertion and Withdrawal (Note 1)
- Static Drive (I<sub>OH</sub>/I<sub>OL</sub>)
  - ±24 mA @ 3.0V V<sub>CC</sub>
  - $\pm 18$  mA @ 2.3V  $V_{CC}$
  - ±6 mA @ 1.65V V<sub>CC</sub>
- Uses patented noise/EMI reduction circuitry
- Functionally compatible with 74 series 16245
- Latchup performance exceeds 300 mA
- ESD performance:
  - Human Body Model >2000V Machine model >200V
- Also packaged in plastic Fine-Pitch Ball Grid Array (FBGA)

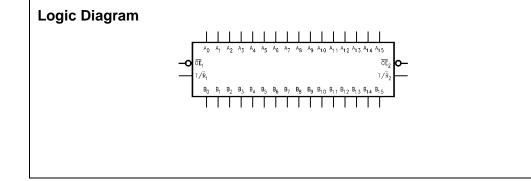
Note 1: To ensure the high impedance state during power up or power down,  $OE_n$  should be tied to  $V_{CCB}$  through a pull up resistor. The minimum value of the resistor is determined by the current sourcing capability of the driver.

## **Ordering Code:**

Order Number	Package Number	Package Description
74VCX164245GX (Note 2)	BGA54A	54-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide [Tape and Reel]
74VCX164245MTD (Note 3)	MTD48	48-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide

Note 2: BGA package available in Tape and Reel only.

Note 3: Device also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering code.



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**Connection Diagrams** 



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Pin Ass	signment fo	r TSSOP
1/R <sub>1</sub> —		48 0E1
B <sub>0</sub> —	2	47 A <sub>0</sub>
B1 —	3	46 A1
GND -	4	45 GND
В <sub>2</sub> —	5	44 - A <sub>2</sub>
в <sub>3</sub> —	6	43 A3
V <sub>CCB</sub> —	7	42 V <sub>CCA</sub>
B4 —	8	41 — A <sub>4</sub>
в <sub>5</sub> —	9	40 A <sub>5</sub>
GND —	10	39 — GND
в <sub>6</sub> —	11	38 — A <sub>6</sub>
в <sub>7</sub> —	12	37 — A <sub>7</sub>
B <sub>8</sub> —	13	36 — A <sub>8</sub>
в <sub>9</sub> —	14	35 — Ag
GND —	15	34 — GND
B <sub>10</sub> —	16	33 A <sub>10</sub>
B <sub>11</sub> —	17	32 — A <sub>11</sub>
v <sub>ссв</sub> —	18	31 — V <sub>CCA</sub>
B <sub>12</sub> —	19	30 — A <sub>12</sub>
B <sub>13</sub> —	20	29 A <sub>13</sub>
GND —	21	28 GND
B <sub>14</sub> —	22	27 — A <sub>14</sub>
B <sub>15</sub> —	23	26 <u>A<sub>15</sub></u>
t/R <sub>2</sub> —	24	25 - 0E <sub>2</sub>
I		
Pin As	signment fo	r FBGA
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#### **Pin Descriptions**

Pin Names	Description
<del>OE</del> n	Output Enable Input (Active LOW)
T/R <sub>n</sub>	Transmit/Receive Input
A <sub>0</sub> –A <sub>15</sub> B <sub>0</sub> –B <sub>15</sub>	Side A Inputs or 3-STATE Outputs
B <sub>0</sub> -B <sub>15</sub>	Side B Inputs or 3-STATE Outputs
NC	No Connect

#### **FBGA Pin Assignments**

	1	2	3	4	5	6
Α	B <sub>0</sub>	NC	T/R <sub>1</sub>	OE <sub>1</sub>	NC	A <sub>0</sub>
В	B <sub>2</sub>	B <sub>1</sub>	NC	NC	A <sub>1</sub>	A <sub>2</sub>
С	B <sub>4</sub>	B <sub>3</sub>	V <sub>CCB</sub>	V <sub>CCA</sub>	A <sub>3</sub>	A <sub>4</sub>
D	B <sub>6</sub>	B <sub>5</sub>	GND	GND	A <sub>5</sub>	A <sub>6</sub>
E	B <sub>8</sub>	В <sub>7</sub>	GND	GND	A <sub>7</sub>	A <sub>8</sub>
F	B <sub>10</sub>	B <sub>9</sub>	GND	GND	A <sub>9</sub>	A <sub>10</sub>
G	B <sub>12</sub>	B <sub>11</sub>	V <sub>CCB</sub>	V <sub>CCA</sub>	A <sub>11</sub>	A <sub>12</sub>
Н	B <sub>14</sub>	B <sub>13</sub>	NC	NC	A <sub>13</sub>	A <sub>14</sub>
J	B <sub>15</sub>	NC	T/R <sub>2</sub>	OE <sub>2</sub>	NC	A <sub>15</sub>

#### **Truth Tables**

Inputs		
OE <sub>1</sub>	T/R <sub>1</sub>	Outputs
L	L	Bus $B_0-B_7$ Data to Bus $A_0-A_7$
L	Н	Bus $A_0 - A_7$ Data to Bus $B_0 - B_7$
н	Х	HIGH Z State on A <sub>0</sub> –A <sub>7</sub> , B <sub>0</sub> –B <sub>7</sub>
Inp	outs	<b>.</b>
	outs T/R <sub>2</sub>	Outputs
<u> </u>	_	Outputs Bus B <sub>8</sub> –B <sub>15</sub> Data to Bus A <sub>8</sub> –A <sub>15</sub>
<u> </u>	_	

(Top Thru View)

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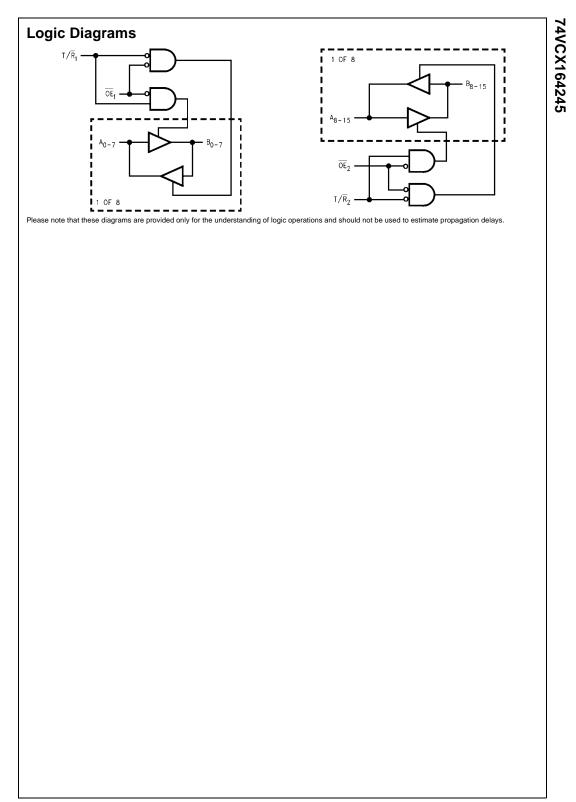
H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial (HIGH or LOW, inputs may not float) Z = High Impedance

### **Translator Power Up Sequence Recommendations**

To guard against power up problems, some simple guidelines need to be adhered to. The VCX164245 is designed so that the control pins (T/ $R_n$ ,  $\overline{OE}_n$ ) are supplied by V<sub>CCB</sub>. Therefore the first recommendation is to begin by powering up the control side of the device, V<sub>CCB</sub>. The  $\overline{OE}_n$  control pins should be ramped with or ahead of V<sub>CCB</sub>, this will guard against bus contentions and oscillations as all A Port and B Port outputs will be disabled. To ensure the high impedance state during power up or power down,  $\overline{OE}_n$ should be tied to V<sub>CCB</sub> through a pull up resistor. The minimum value of the resistor is determined by the current sourcing capability of the driver. Second, the  $T/\overline{R}_n$  control pins should be placed at logic low (0V) level, this will ensure that the B-side bus pins are configured as inputs to help guard against bus contention and oscillations. B-side Data Inputs should be driven to a valid logic level (0V or  $V_{CCB}$ ), this will prevent excessive current draw and oscillations.  $V_{CCB}$ , this will prevent excessive current draw and oscillations. V<sub>CCB</sub>, but should never exceed the  $V_{CCB}$  voltage level. Upon completion of these steps the device can then be configured for the users desired operation. Following these steps will help to prevent possible damage to the translator device as well as other system components.



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## Absolute Maximum Ratings(Note 4)

# Recommended Operating Conditions (Note 6)

Supply Voltage		Conditions (Note 6)	
V <sub>CCA</sub>	–0.5V to $V_{CCB}$	Power Supply (Note 7)	
V <sub>CCB</sub>	-0.5V to 4.6V	V <sub>CCA</sub>	1.65V to 2.7V
DC Input Voltage (VI)	-0.5V to +4.6V	V <sub>CCB</sub>	2.3V to 3.6V
DC Output Voltage (V <sub>I/O</sub> )		Input Voltage (V <sub>I</sub> ) @ OE, T/R	0V to V <sub>CCB</sub>
Outputs 3-STATE	-0.5V to +4.6V	Input/Output Voltage (V <sub>I/O</sub> )	
Outputs Active (Note 5)		A <sub>n</sub>	0V to V <sub>CCA</sub>
An	$-0.5V$ to $V_{\mbox{\scriptsize CCA}}+0.5V$	B <sub>n</sub>	0V to V <sub>CCB</sub>
Bn	$-0.5V$ to $V_{\mbox{\scriptsize CCB}}+0.5V$	Output Current in I <sub>OH</sub> /I <sub>OL</sub>	
DC Input Diode Current (I <sub>IK</sub> )		$V_{CCA} = 2.3V$ to 2.7V	±18 mA
V <sub>1</sub> < 0V	–50 mA	V <sub>CCA</sub> = 1.65V to 1.95V	±6 mA
DC Output Diode Current (I <sub>OK</sub> )		$V_{CCB} = 3.0V$ to $3.6V$	±24 mA
V <sub>O</sub> < 0V	–50 mA	$V_{CCB} = 2.3V$ to 2.7V	±18 mA
$V_{O} > V_{CC}$	+50 mA	Free Air Operating Temperature $(T_A)$	$-40^\circ C$ to $+85^\circ C$
DC Output Source/Sink Current	±50 mA	Minimum Input Edge Rate ( $\Delta t/\Delta V$ )	
(I <sub>OH</sub> /I <sub>OL</sub> )		$V_{\text{IN}} = 0.8 \text{V}$ to 2.0V, $V_{\text{CC}} = 3.0 \text{V}$	10 ns/V
DC V <sub>CC</sub> or Ground Current	±100 mA	Note 4: The "Absolute Maximum Ratings" are those	
Supply Pin (I <sub>CC</sub> or Ground)		the safety of the device cannot be guaranteed. The operated at these limits. The parametric values de	
Storage Temperature (T <sub>STG</sub> )	$-65^{\circ}C$ to $+150^{\circ}C$	Characteristics tables are not guaranteed at the abs. The "Recommended Operating Conditions" table w for actual device operation.	

Note 5:  $\mathrm{I}_\mathrm{O}$  Absolute Maximum Rating must be observed.

Note 6: Unused inputs or I/O pins must be held HIGH or LOW. They may not float.

Note 7: Operation requires:  $V_{CCA} \leq V_{CCB}$ 

# DC Electrical Characteristics (1.65V $< V_{CCA} \leq$ 1.95V, 2.3V $< V_{CCB} \leq$ 2.7V)

Symbol	Parameter		Conditions	V <sub>CCA</sub> (V)	V <sub>ССВ</sub> (V)	Min	Max	Units
V <sub>IHA</sub>	HIGH Level Input Voltage	A <sub>n</sub>		1.65-1.95	2.3–2.7	$0.65 \times V_{CC}$		V
V <sub>IHB</sub>		B <sub>n</sub> , T/R, OE		1.65-1.95	2.3–2.7	1.6		V
V <sub>ILA</sub>	LOW Level Input Voltage	A <sub>n</sub>		1.6-1.95	2.3–2.7		$0.35 \times V_{CC}$	V
V <sub>ILB</sub>		B <sub>n</sub> , T/R, OE		1.65-1.95	2.3–2.7		0.7	V
V <sub>OHA</sub>	HIGH Level Output Voltag	e	I <sub>OH</sub> = -100 μA	1.65-1.95	2.3–2.7	V <sub>CCA</sub> -0.2		V
			$I_{OH} = -6 \text{ mA}$	1.65	2.3–2.7	1.25		v
V <sub>OHB</sub>	HIGH Level Output Voltag	е	I <sub>OH</sub> = -100 μA	1.65–1.95	2.3–2.7	V <sub>CCB</sub> -0.2		V
			$I_{OH} = -18 \text{ mA}$	1.65-1.95	2.3	1.7		v
V <sub>OLA</sub>	LOW Level Output Voltage	9	I <sub>OL</sub> = 100 μA	1.65-1.95	2.3–2.7		0.2	V
			$I_{OL} = 6 \text{ mA}$	1.65	2.3–2.7		0.3	v
V <sub>OLB</sub>	LOW Level Output Voltage	9	I <sub>OL</sub> = 100 μA	1.65-1.95	2.3–2.7		0.2	V
			I <sub>OL</sub> = 18 mA	1.65–1.95	2.3		0.6	v
l <sub>l</sub>	Input Leakage Current @	OE, T/R	$0V \le V_I \le 3.6V$	1.65–1.95	2.3–2.7		±5.0	μΑ
oz	3-STATE Output Leakage		$\frac{0V \le V_O \le 3.6V}{\overline{OE}} = V_{CCB}$ $V_I = V_{IH} \text{ or } V_{IL}$	1.65–1.95	2.3–2.7		±10	μA
OFF	Power OFF Leakage Curr	ent	$0 \le (V_I, V_O) \le 3.6V$	0	0		10	μA
CCA/ICCB	Quiescent Supply Current per supply, V <sub>CCA</sub> / V <sub>CCB</sub>		$A_n = V_{CCA}$ or GND $B_n$ , $\overline{OE}$ , & $T/\overline{R} = V_{CCB}$ or GND	1.65–1.95	2.3–2.7		20	μA
			$\label{eq:V_CCA} \begin{split} & V_{CCA} \leq A_n \leq 3.6V \\ & V_{CCB} \leq B_n, \ \overline{OE}, \ T/\overline{R} \leq 3.6V \end{split}$	1.65–1.95	2.3–2.7		±20	μA
۵I <sub>CC</sub>	Increase in I <sub>CC</sub> per Input,	B <sub>n</sub> , T/R, OE	$V_I = V_{CCB} - 0.6V$	1.65–1.95	2.3–2.7		750	μΑ
	Increase in I <sub>CC</sub> per Input, An		$V_I = V_{CCA} - 0.6V$	1.65-1.95	2.3-2.7		750	μA

Symbol	Pa	arameter	Conditions	V <sub>CCA</sub> (V)	V <sub>ССВ</sub> (V)	Min	Мах	Units
V <sub>IHA</sub>	HIGH Level	A <sub>n</sub>		1.65–1.95	3.0–3.6	$0.65 \times V_{CC}$		V
V <sub>IHB</sub>	Input Voltage	B <sub>n</sub> , T/R, OE		1.65–1.95	3.0–3.6	2.0		V
V <sub>ILA</sub>	LOW Level	A <sub>n</sub>		1.65–1.95	3.0–3.6		$0.35 \times V_{CC}$	V
V <sub>ILB</sub>	Input Voltage	B <sub>n</sub> , T/R, OE		1.65–1.95	3.0–3.6		0.8	V
V <sub>OHA</sub>	HIGH Level Outp	out Voltage	I <sub>OH</sub> = -100 μA	1.65–1.95	3.0–3.6	V <sub>CCA</sub> -0.2		V
			$I_{OH} = -6 \text{ mA}$	1.65	3.0-3.6	1.25		v
V <sub>OHB</sub>	HIGH Level Outp	out Voltage	I <sub>OH</sub> = -100 μA	1.65-1.95	3.0–3.6	V <sub>CCA</sub> -0.2		v
			$I_{OH} = -24 \text{ mA}$	1.65-1.95	3.0	2.2		v
V <sub>OLA</sub>	LOW Level Output Volta	ut Voltage	I <sub>OL</sub> = 100 μA	1.65-1.95	3.0–3.6		0.2	v
			$I_{OL} = 6 \text{ mA}$	1.65	3.0-3.6		0.3	v
V <sub>OLB</sub>	LOW Level Output Voltage		I <sub>OL</sub> = 100 μA	1.65–1.95	3.0–3.6		0.2	v
			$I_{OL} = 24 \text{ mA}$	1.65–1.95	3.0		0.55	v
l <sub>l</sub>	Input Leakage Current @ OE, T/R		$0V \le V_I \le 3.6V$	1.65–1.95	3.0–3.6		±5.0	μA
I <sub>OZ</sub>	3-STATE Output	Leakage	$0V \le V_O \le 3.6V$					
			$OE^* = V_{CCB}$	1.65-1.95	3.0–3.6		±10	μΑ
			$V_I = V_{IH} \text{ or } V_{IL}$					
I <sub>OFF</sub>	Power Off Leakage Current		$0 \le (V_I, V_O) \le 3.6V$	0	0		10	μΑ
I <sub>CCA</sub> /I <sub>CCB</sub>	Quiescent Suppl	y Current,	$A_n = V_{CCA}$ or GND	1.65-1.95	3.0-3.6		20	μA
	per supply, $V_{CCA}$	V <sub>CCB</sub>	$B_n$ , $\overline{OE}$ , & $T/R = V_{CCB}$ or GND	1.00 1.00	0.0 0.0		20	μι
			$V_{CCA} \le A_n \le 3.6V$	1.65-1.95	3.0–3.6		±20	μA
			$V_{CCB} \le B_n$ , $\overline{OE}$ , $T/R \le 3.6V$					, r.r.
ΔI <sub>CC</sub>	Increase in I <sub>CC</sub> p	er Input, B <sub>n</sub> , T/R, OE	$V_I = V_{CCB} - 0.6V$	1.65–1.95	3.0–3.6		750	μA
	Increase in I <sub>CC</sub> p	er Input, A <sub>n</sub>	$V_I = V_{CCA} - 0.6V$	1.65-1.95	3.0-3.6		750	μA

# DC Electrical Characteristics (2.3V < V\_{CCA} $\leq$ 2.7V, 3.0V $\leq$ V\_{CCB} $\leq$ 3.6V)

Symbol	Parameter		Conditions	V <sub>CCA</sub> (V)	V <sub>ССВ</sub> (V)	Min	Max	Units	
V <sub>IHA</sub>	HIGH Level Input Voltage	A <sub>n</sub>		2.3–2.7	3.0-3.6	1.6		V	
V <sub>IHB</sub>		B <sub>n</sub> , T/R, OE		2.3–2.7	3.0-3.6	2.0		V	
V <sub>ILA</sub>	LOW Level Input Voltage	A <sub>n</sub>		2.3–2.7	3.0-3.6		0.7	V	
V <sub>ILB</sub>		B <sub>n</sub> , T/R, OE		2.3–2.7	3.0-3.6		0.8	V	
V <sub>OHA</sub>	HIGH Level Output Voltag	e	I <sub>OH</sub> = -100 μA	2.3–2.7	3.0-3.6	V <sub>CCA</sub> -0.2		V	
			I <sub>OH</sub> = -18 mA	2.3	3.0-3.6	1.7		v	
V <sub>OHB</sub>	HIGH Level Output Voltag	е	I <sub>OH</sub> = -100 μA	2.3–2.7	3.0-3.6	V <sub>CCB</sub> -0.2		v	
			$I_{OH} = -24 \text{ mA}$	2.3–2.7	3.0	2.2		v	
V <sub>OLA</sub>	LOW Level Output Voltage	Э	I <sub>OL</sub> = 100 μA	2.3–2.7	3.0–3.6		0.2	V	
			I <sub>OL</sub> = 18 mA	2.3	3.0-3.6		0.6	v	
V <sub>OLB</sub>	LOW Level Output Voltage	Э	$I_{OL} = 100 \ \mu A$	2.3–2.7	3.0-3.6		0.2	V	
			$I_{OL} = 24 \text{ mA}$	2.3–2.7	3.0		0.55	v	
l <sub>l</sub>	Input Leakage Current @	OE, T/R	$0V \le V_I \le 3.6V$	2.3–2.7	3.0–3.6		±5.0	μΑ	
l <sub>oz</sub>	3-STATE Output Leakage	@ A <sub>n</sub>	$\frac{0V \le V_O \le 3.6V}{\overline{OE}} = V_{CCA}$ $V_I = V_{IH} \text{ or } V_{IL}$	2.3–2.7	3.0–3.6		±10	μA	
I <sub>OFF</sub>	Power OFF Leakage Curr	ent	$0 \le (V_I, V_O) \le 3.6V$	0	0		10	μΑ	
I <sub>CCA</sub> /I <sub>CCB</sub>	Quiescent Supply Current per supply, V <sub>CCA</sub> /V <sub>CCB</sub>	9	$A_n = V_{CCA}$ or GND $B_n$ , $\overline{OE}$ , & $T/\overline{R} = V_{CCB}$ or GND	2.3–2.7	3.0–3.6		20	μA	
			$V_{CCA} \le A_n \le 3.6V$ $V_{CCB} \le B_n$ , $\overline{OE}$ , $T/\overline{R} \le 3.6V$	2.3–2.7	3.0–3.6		±20	μA	
ΔI <sub>CC</sub>	Increase in I <sub>CC</sub> per Input,	B <sub>n</sub> , T/R, OE	$V_I = V_{CCB} - 0.6V$	2.3–2.7	3.0–3.6		750	μΑ	
	Increase in I <sub>CC</sub> per Input,	A <sub>n</sub>	$V_{I} = V_{CCA} - 0.6V$	2.3-2.7	3.0-3.6		750	μA	

			C <sub>L</sub> = 30 p	oF, R <sub>L</sub> = 5000	$\mathbf{P}$ , $\mathbf{T}_{\mathbf{A}} = -40^{\circ}\mathbf{C}$	to +85°C,		
Symbol	Parameter	V <sub>CCA</sub> = 1.6	$V_{CCA} = 1.65V \text{ to } 1.95V$ $V_{CCB} = 2.3V \text{ to } 2.7V$		5V to 1.95V	V <sub>CCA</sub> = 2.3V to 2.7V		Units
-,		V <sub>CCB</sub> = 2.			$V_{CCB} = 3.0V$ to $3.6V$		$V_{CCB} = 3.0V$ to $3.6V$	
		Min	Max	Min	Max	Min	Max	
t <sub>PHL</sub> , t <sub>PLH</sub>	Prop Delay, A to B	0.8	5.5	0.6	5.1	0.6	4.0	ns
t <sub>PHL</sub> , t <sub>PLH</sub>	Prop Delay, B to A	1.5	5.8	1.5	6.2	0.8	4.4	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time, OE to B	0.8	5.3	0.6	5.1	0.6	4.0	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time, OE to A	1.5	8.3	1.5	8.2	0.8	4.6	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time, OE to B	0.8	5.2	0.8	5.6	0.8	4.8	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time, OE to A	0.8	4.6	0.8	4.5	0.8	4.4	ns
t <sub>osHL</sub> t <sub>osLH</sub>	Output to Output Skew (Note 8)		0.5		0.5		0.75	ns

Note 8: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW ( $t_{osHL}$ ) or LOW-to-HIGH ( $t_{osLH}$ ).

# **Dynamic Switching Characteristics**

Symbol	Parameter	Conditions	V <sub>CCA</sub>	V <sub>CCB</sub>	$T_A = 25^{\circ}C$	Units	
Gymbol	i aranieter	Conditions	(V)	(V)	Typical	onno	
V <sub>OLP</sub>	Quiet Output Dynamic Peak V <sub>OL</sub> ,	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	0.25		
	B to A		1.8	3.3	0.25	V	
			2.5	3.3	0.6		
	Quiet Output Dynamic Peak V <sub>OL</sub> ,	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	0.6		
	A to B		1.8	3.3	0.8	V	
			2.5	3.3	0.8		
V <sub>OLV</sub>	Quiet Output Dynamic Valley V <sub>OL</sub> ,	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	-0.25		
	B to A		1.8	3.3	-0.25	V	
			2.5	3.3	-0.6		
	Quiet Output Dynamic Valley V <sub>OL</sub> ,	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	-0.6		
	A to B		1.8	3.3	-0.8	V	
			2.5	3.3	-0.8		
V <sub>OHV</sub>	Quiet Output Dynamic Valley V <sub>OH</sub> ,	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	1.7		
	A to B		1.8	3.3	2.0	V	
			2.5	3.3	2.0		
	Quiet Output Dynamic Valley V <sub>OH</sub> ,	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	1.3		
	B to A		1.8	3.3	1.3	V	
			2.5	3.3	1.7		

## Capacitance

Symbol	Parameter	Conditions	$T_A = +25^{\circ}C$ Typical	Units
CIN	Input Capacitance	$V_{CCA} = 2.5V$ , $V_{CCB} = 3.3V$ , $V_I = 0V$ or $V_{CCA/B}$	5	pF
C <sub>I/O</sub>	Input/Output Capacitance	$V_{CCA} = 2.5V$ , $V_{CCB} = 3.3V$ , $V_I = 0V$ or $V_{CCA/B}$	6	pF
C <sub>PD</sub>	Power Dissipation Capacitance	$V_{CCA} = 2.5V, V_{CCB} = 3.3V, V_I = 0V \text{ or } V_{CCA/B}$ f = 10 MHz	20	pF

